

Silicon Diode

BYD17K

800V/1.5A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

Controlled avalanche rectifiers

BYD17 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier outline.

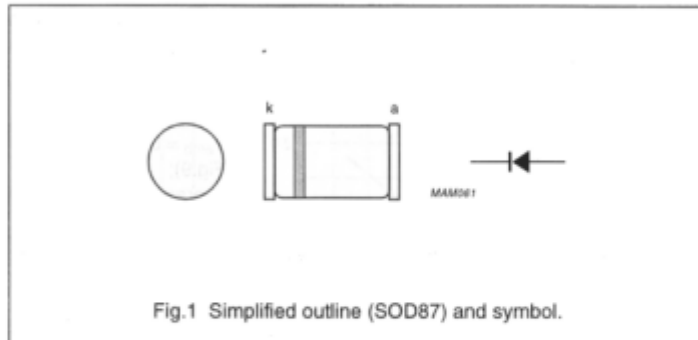


Fig.1 Simplified outline (SOD87) and symbol.

DESCRIPTION

Cavity free cylindrical glass package through Implotec™(1) technology.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

MARKING

TYPE NUMBER	MARKING CODE
BYD17D	17D PH
BYD17G	17G PH
BYD17J	17J PH
BYD17K	17K PH
BYD17M	17M PH

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BYD17D		–	200	V
	BYD17G		–	400	V
	BYD17J		–	600	V
	BYD17K		–	800	V
V_{RWM}	crest working reverse voltage				
	BYD17D		–	200	V
	BYD17G		–	400	V
	BYD17J		–	600	V
	BYD17K		–	800	V
V_R	continuous reverse voltage				
	BYD17D		–	200	V
	BYD17G		–	400	V
	BYD17J		–	600	V
	BYD17K		–	800	V
	BYD17M		–	1000	V

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{F(AV)}$	average forward current	$T_{tp} = 105\text{ °C}$; averaged over any 20 ms period; see Figs 2 and 4	–	1.5	A
		$T_{amb} = 65\text{ °C}$; PCB mounting (see Fig.9); averaged over any 20 ms period; see Figs 3 and 4	–	0.6	A
I_{FSM}	non-repetitive peak forward current	$t = 10\text{ ms}$ half sinewave; $T_j = T_{jmax}$ prior to surge; $V_R = V_{RRMmax}$	–	20	A
E_{RSM}	non-repetitive peak reverse avalanche energy	$L = 120\text{ mH}$; $T_j = T_{jmax}$ prior to surge; inductive load switched off	–	7	mJ
T_{stg}	storage temperature		–65	+175	°C
T_j	junction temperature	see Fig.5	–65	+175	°C

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
V_F	forward voltage	$I_F = 1\text{ A}$; $T_j = T_{jmax}$; see Fig.6	–	–	0.93	V	
		$I_F = 1\text{ A}$; see Fig.6	–	–	1.05	V	
$V_{(BR)R}$	reverse avalanche breakdown voltage	$I_R = 0.1\text{ mA}$					
			BYD17D	225	–	–	V
			BYD17G	450	–	–	V
			BYD17J	650	–	–	V
			BYD17K	900	–	–	V
			BYD17M	1100	–	–	V
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig.7	–	–	1	μA	
		$V_R = V_{RRMmax}$; $T_j = 165\text{ °C}$; see Fig.7	–	–	100	μA	
t_{rr}	reverse recovery time	when switched from $I_F = 0.5\text{ A}$ to $I_R = 1\text{ A}$; measured at $I_R = 0.25\text{ A}$; see Fig.10	–	3	–	μs	
C_d	diode capacitance	$V_R = 0\text{ V}$; $f = 1\text{ MHz}$; see Fig.8	–	21	–	pF	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		30	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	150	K/W

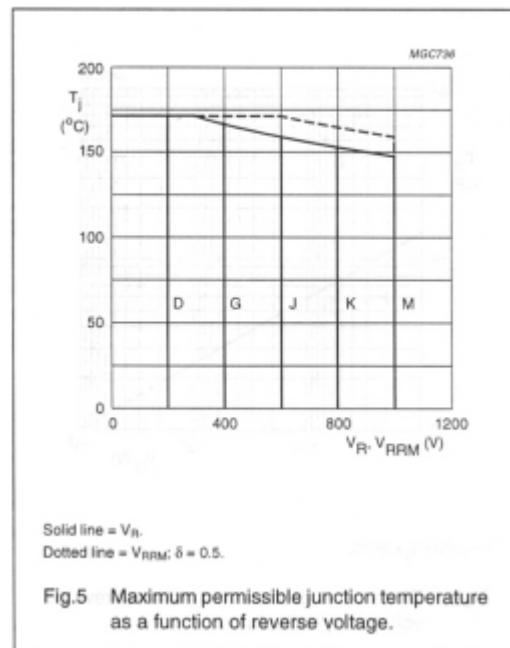
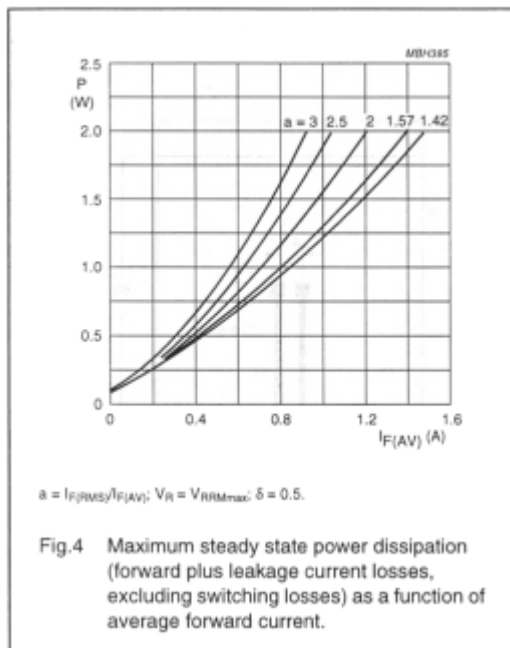
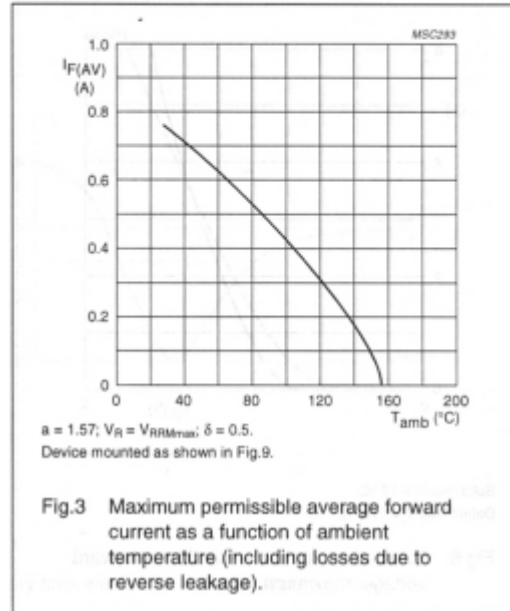
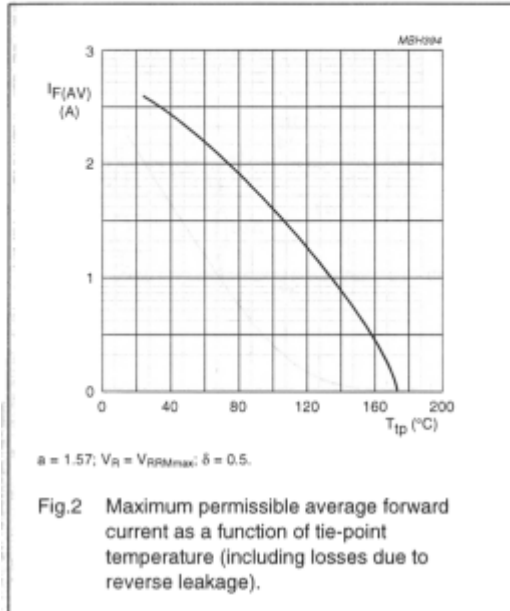
Note

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper $\geq 40\text{ μm}$, see Fig.9. For more information please refer to the "General Part of Handbook SC01".

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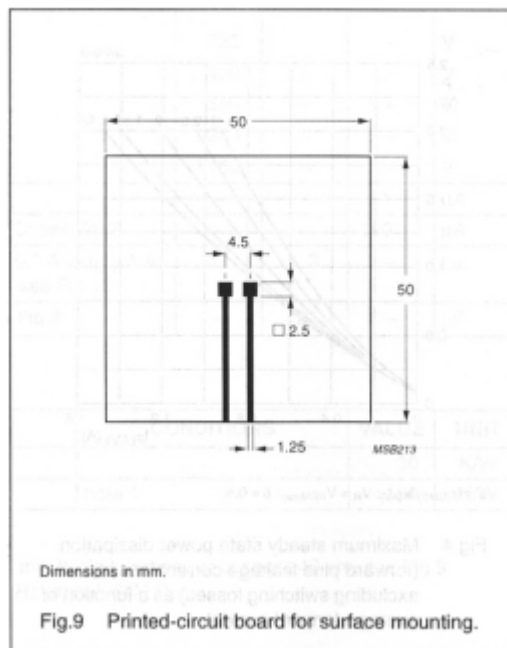
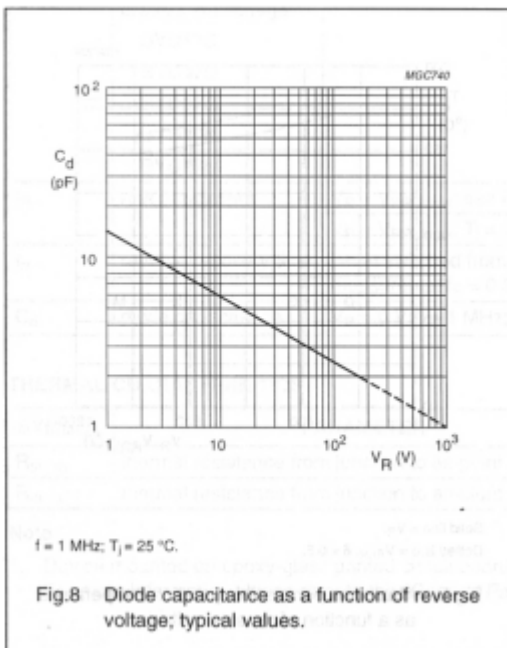
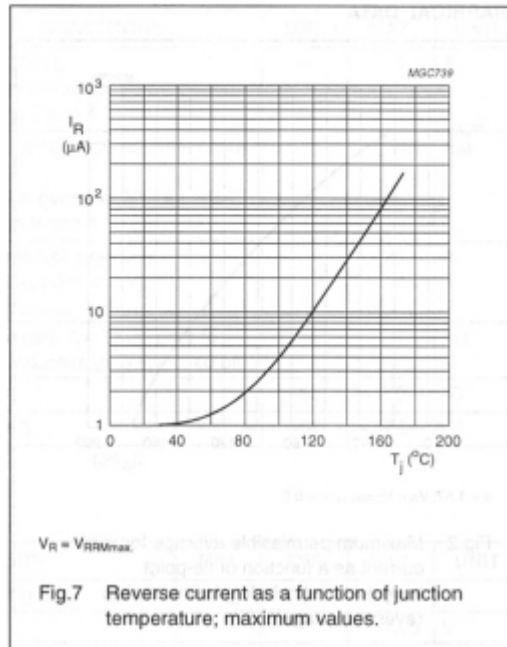
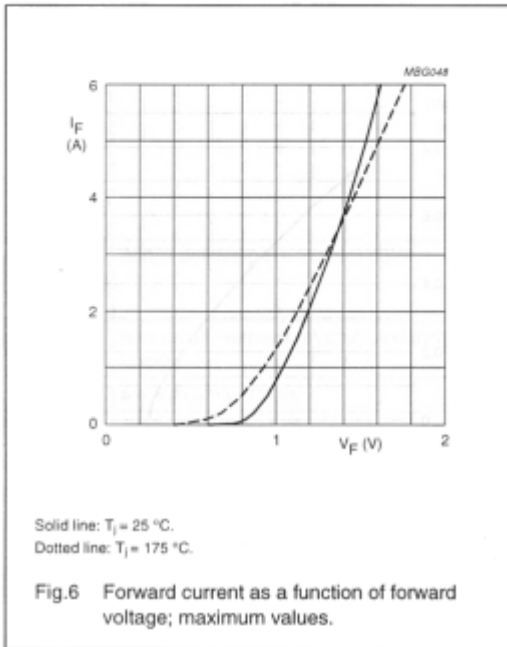
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GRAPHICAL DATA



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